

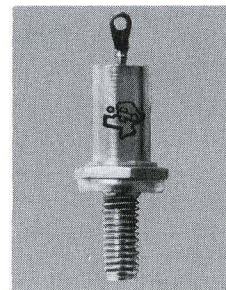
TYPES 1N1130 AND 1N1131 SINGLE JUNCTION SILICON RECTIFIERS



TYPES 1N1130 AND 1N1131
BULLETIN NO. DL-S 907
REPLACES BULLETIN NO. DL-S 724
MAY, 1958

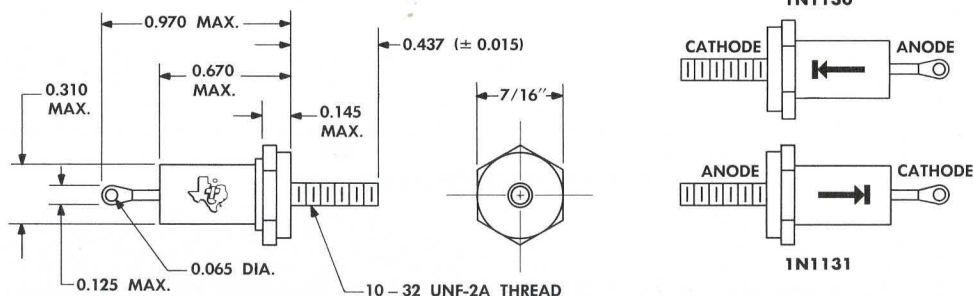
1500 VOLTS • 300 mA

Designed to meet stringent military requirements
Ideal for miniaturization
Available with anode to stud or cathode to stud



mechanical data

Welded case with glass-to-metal seal between case and lead. Approximate weight is 5.9 grams.



absolute maximum ratings

e _{px}	Recurrent Peak Inverse Voltage at +25°C*	1500 V
I _o	Average Rectified Forward Current at +25°C*†	300 mA
i _i	Recurrent Peak Current at -65°C to +150°C†	1 A
	Stud Temperature	165 °C
	Altitude*	70,000 ft
T _A	Operating Temperature, Ambient	-65°C to +150°C

electrical specifications

D.C. Test at 25°C

LI _b	Maximum Reverse Leakage Current at E _b = -1500 Vdc	50 μA
E _b	Maximum Forward Voltage Drop at I _o = 300 mA	15 V

*Refer to characteristic curves.

†Mounted on a 2.5" x 2.5" x 1/8" aluminum heat sink.

LICENSED UNDER BELL SYSTEM PATENTS

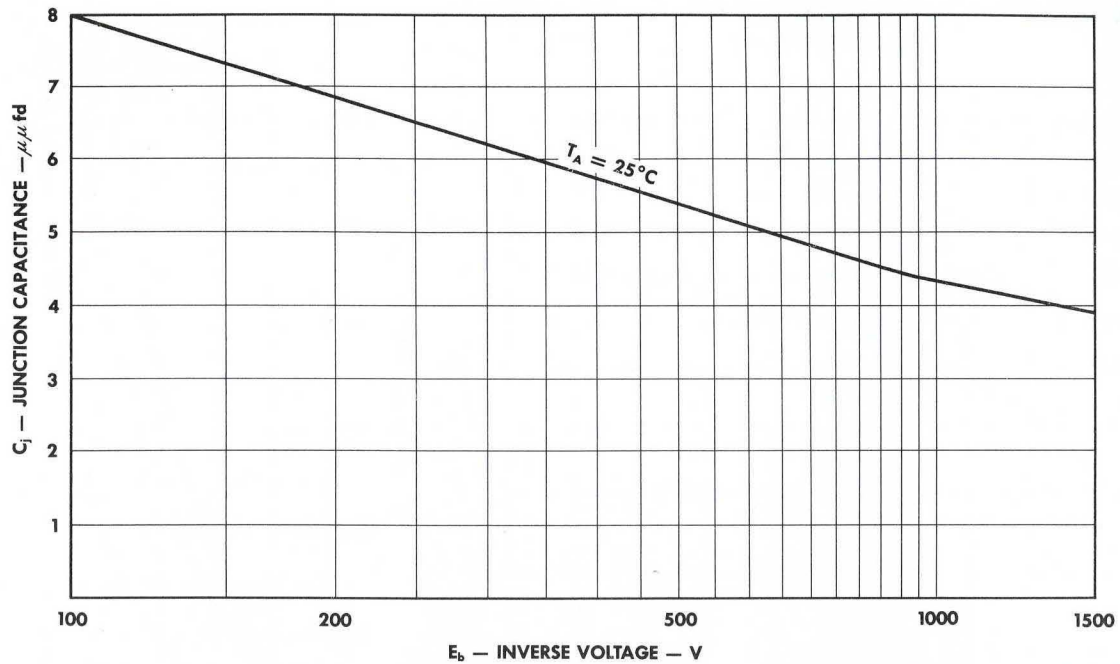
SEMICONDUCTOR-COMPONENTS DIVISION

14722

TEXAS INSTRUMENTS
INCORPORATED
POST OFFICE BOX 312 • DALLAS, TEXAS

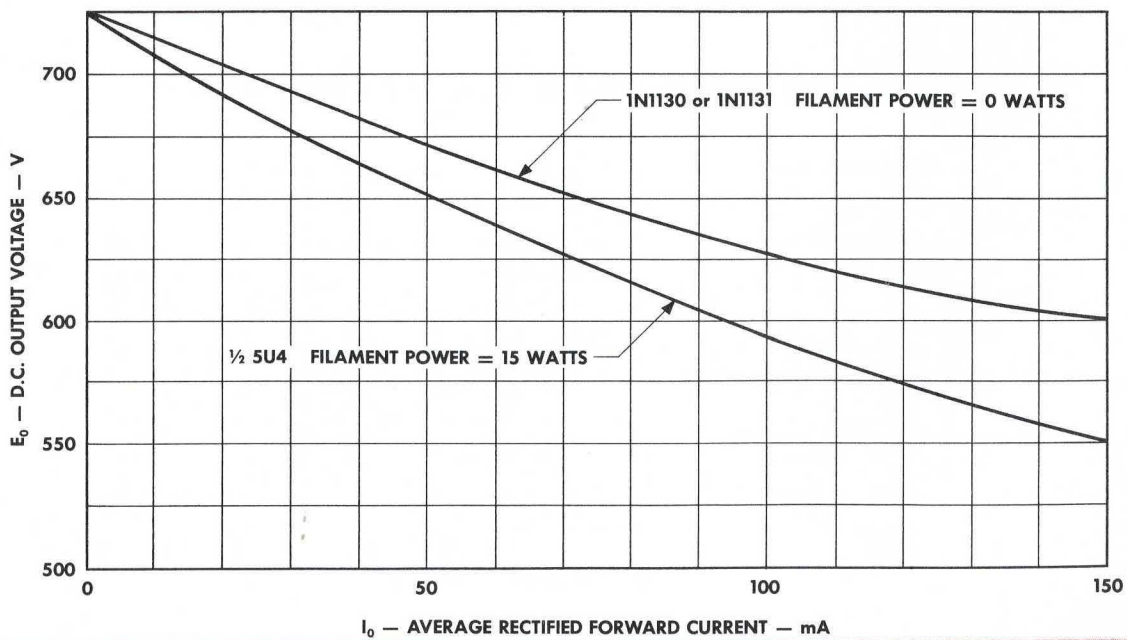
TYPES 1N1130 AND 1N1131

TYPICAL D.C. JUNCTION CAPACITANCE CHARACTERISTICS

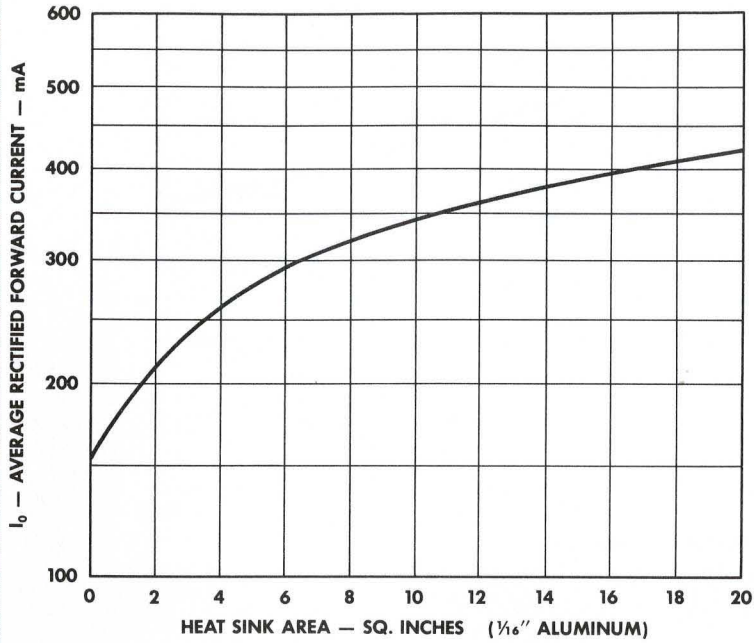


TYPICAL EFFICIENCY COMPARISON WITH HALF OF A 5U4 VACUUM TUBE

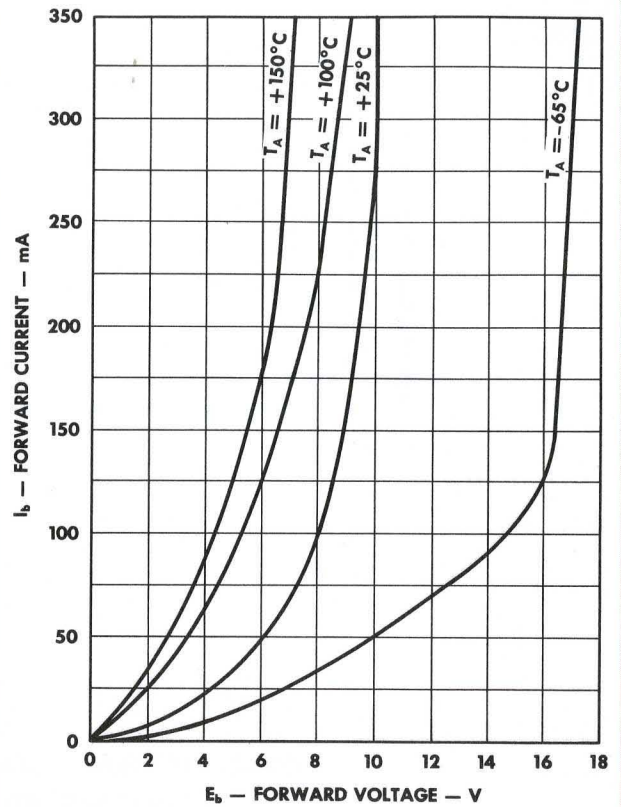
(HALF-WAVE CIRCUIT WITH CAPACITIVE INPUT AT 1500 VOLTS PIV AT 25°C)



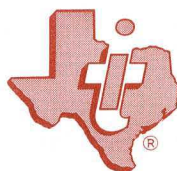
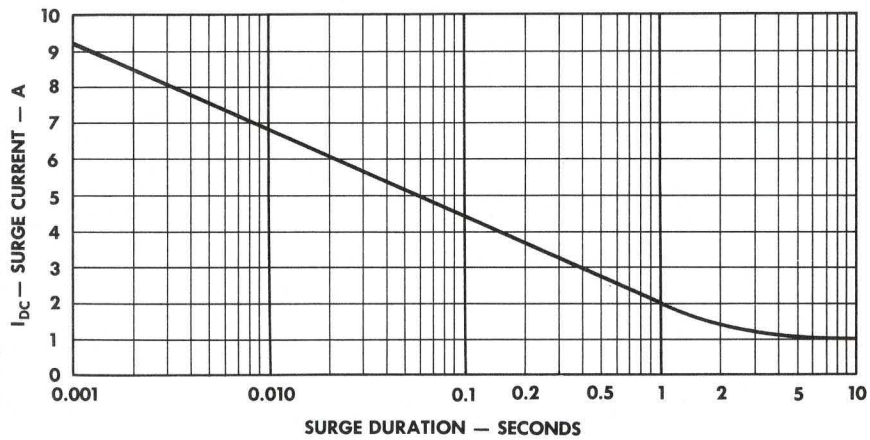
AVERAGE RECTIFIED CURRENT VERSUS HEAT SINK AREA
(STILL AIR: $T_A = 25^\circ\text{C}$)



TYPICAL STATIC FORWARD CHARACTERISTICS



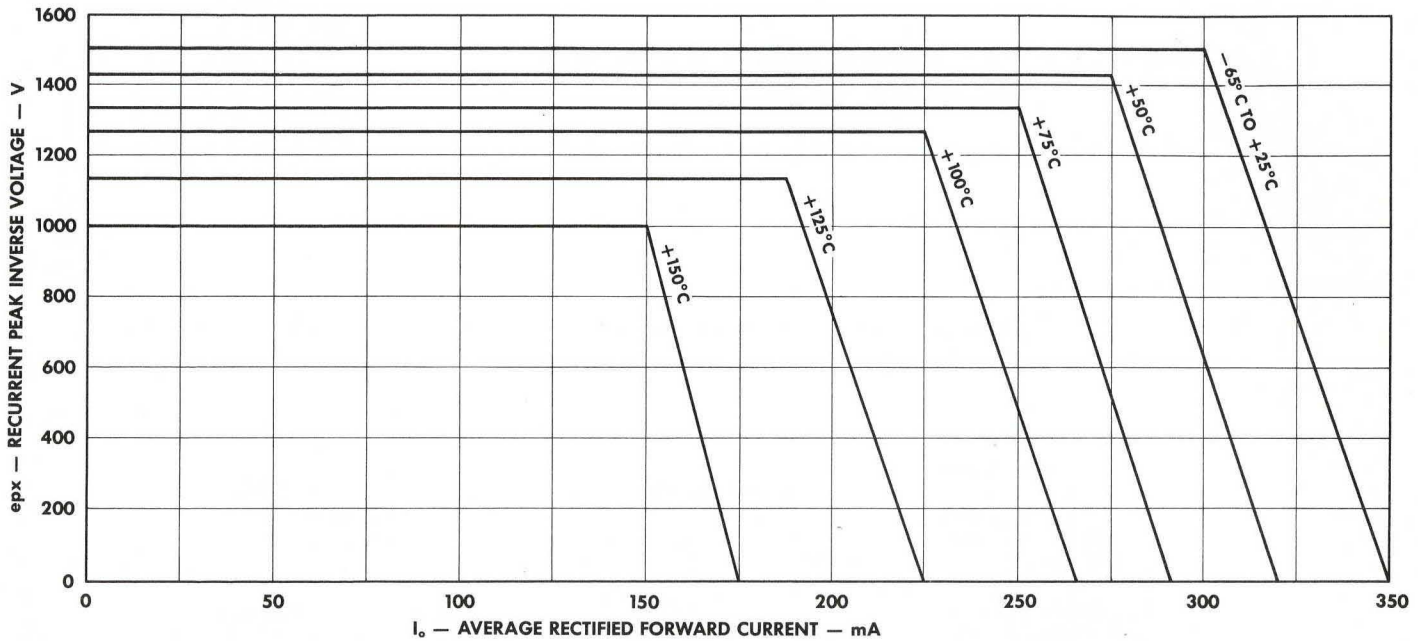
NON-REPETITIVE SURGE CURRENT RATINGS AT 25°C



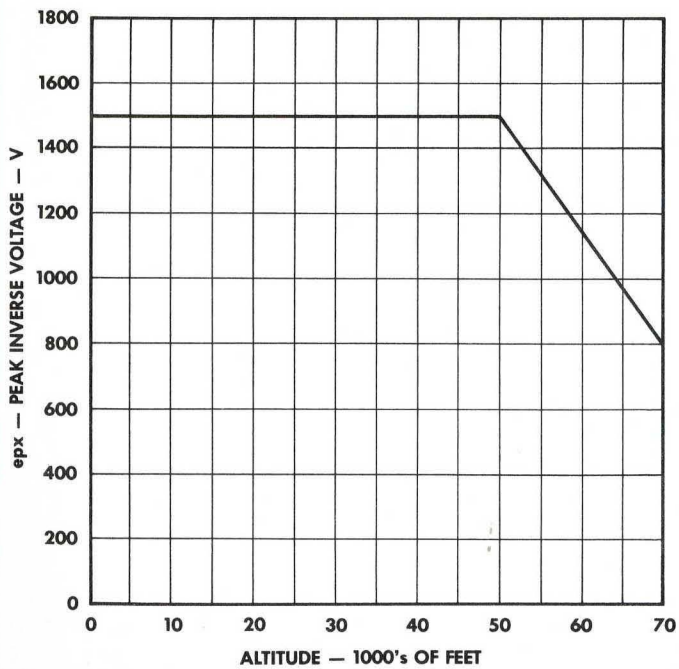
TYPES 1N1130 AND 1N1131

OPERATING VOLTAGE AND CURRENT RATINGS WITH TEMPERATURE

(MOUNTED ON A 2.5" x 2.5" x 1/16" ALUMINUM HEAT SINK)



PEAK INVERSE VOLTAGE RATING WITH ALTITUDE



TYPICAL STATIC REVERSE CHARACTERISTICS

